

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

CoolMOS™ C7

650V CoolMOS™ C7 Power Transistor
IPP65R225C7

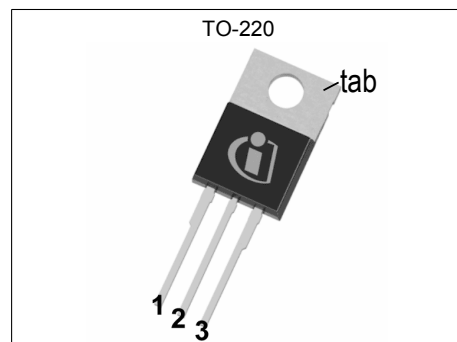
Data Sheet

Rev. 2.0
Final

1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies.

CoolMOS™ C7 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The product portfolio provides all benefits of fast switching superjunction MOSFETs offering better efficiency, reduced gate charge, easy implementation and outstanding reliability.



Features

- Increased MOSFET dv/dt ruggedness
- Better efficiency due to best in class FOM $R_{DS(on)} \cdot E_{oss}$ and $R_{DS(on)} \cdot Q_g$
- Best in class $R_{DS(on)}$ /package
- Easy to use/drive
- Pb-free plating, halogen free mold compound
- Qualified for industrial grade applications according to JEDEC (J-STD20 and JESD22)

Benefits

- Enabling higher system efficiency
- Enabling higher frequency / increased power density solutions
- System cost / size savings due to reduced cooling requirements
- Higher system reliability due to lower operating temperatures

Applications

PFC stages and hard switching PWM stages for e.g. Computing, Server, Telecom, UPS and Solar.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.



Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	700	V
$R_{DS(on),max}$	225	mΩ
$Q_{g,typ}$	20	nC
$I_{D,pulse}$	41	A
$E_{oss}@400V$	2.3	μJ
Body diode di/dt	55	A/μs

Type / Ordering Code	Package	Marking	Related Links
IPP65R225C7	PG-TO 220	65C7225	see Appendix A

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2 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	11 7	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	41	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	48	mJ	$I_D=4.8\text{A}$; $V_{DD}=50\text{V}$
Avalanche energy, repetitive	E_{AR}	-	-	0.24	mJ	$I_D=4.8\text{A}$; $V_{DD}=50\text{V}$
Avalanche current, single pulse	I_{AS}	-	-	4.8	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	100	V/ns	$V_{DS}=0\dots400\text{V}$
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC ($f>1\text{ Hz}$)
Power dissipation	P_{tot}	-	-	63	W	$T_C=25^\circ\text{C}$
Storage temperature	T_{stg}	-55	-	150	$^\circ\text{C}$	-
Operating junction temperature	T_j	-55	-	150	$^\circ\text{C}$	-
Mounting torque	-	-	-	60	Ncm	M3 and M3.5 screws
Continuous diode forward current	I_S	-	-	11	A	$T_C=25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	41	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	1	V/ns	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$
Maximum diode commutation speed	di/dt	-	-	55	A/ μs	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$
Insulation withstand voltage	V_{ISO}	-	-	n.a.	V	V_{rms} , $T_C=25^\circ\text{C}$, $t=1\text{min}$

¹⁾ Limited by $T_{j,max}$.

²⁾ Pulse width t_p limited by $T_{j,max}$.

³⁾ Identical low side and high side switch with identical R_G .

3 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	1.99	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	°C/W	leaded
Thermal resistance, junction - ambient for SMD version	R_{thJA}	-	-	-	°C/W	n.a.
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	1.6mm (0.063 in.) from case for 10s

4 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	650	-	-	V	$V_{GS}=0V$, $I_D=1mA$
Gate threshold voltage	$V_{(GS)th}$	3	3.5	4	V	$V_{DS}=V_{GS}$, $I_D=0.24mA$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=650$, $V_{GS}=0V$, $T_j=25^\circ\text{C}$ $V_{DS}=650$, $V_{GS}=0V$, $T_j=150^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20V$, $V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.199 0.478	0.225 -	Ω	$V_{GS}=10V$, $I_D=4.8A$, $T_j=25^\circ\text{C}$ $V_{GS}=10V$, $I_D=4.8A$, $T_j=150^\circ\text{C}$
Gate resistance	R_G	-	1.2	-	Ω	$f=1MHz$, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	996	-	pF	$V_{GS}=0V$, $V_{DS}=400V$, $f=250kHz$
Output capacitance	C_{oss}	-	14	-	pF	$V_{GS}=0V$, $V_{DS}=400V$, $f=250kHz$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	29	-	pF	$V_{GS}=0V$, $V_{DS}=0...400V$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	313	-	pF	$I_D=\text{constant}$, $V_{GS}=0V$, $V_{DS}=0...400V$
Turn-on delay time	$t_{d(on)}$	-	9	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=4.8A$, $R_G=10\Omega$
Rise time	t_r	-	6	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=4.8A$, $R_G=10\Omega$
Turn-off delay time	$t_{d(off)}$	-	48	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=4.8A$, $R_G=10\Omega$
Fall time	t_f	-	10	-	ns	$V_{DD}=400V$, $V_{GS}=13V$, $I_D=4.8A$, $R_G=10\Omega$

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	5	-	nC	$V_{DD}=400V$, $I_D=4.8A$, $V_{GS}=0$ to $10V$
Gate to drain charge	Q_{gd}	-	6	-	nC	$V_{DD}=400V$, $I_D=4.8A$, $V_{GS}=0$ to $10V$
Gate charge total	Q_g	-	20	-	nC	$V_{DD}=400V$, $I_D=4.8A$, $V_{GS}=0$ to $10V$
Gate plateau voltage	$V_{plateau}$	-	5.4	-	V	$V_{DD}=400V$, $I_D=4.8A$, $V_{GS}=0$ to $10V$

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0V$, $I_F=4.8A$, $T_j=25^{\circ}C$
Reverse recovery time	t_{rr}	-	890	-	ns	$V_R=400V$, $I_F=11A$, $di_F/dt=55A/\mu s$
Reverse recovery charge	Q_{rr}	-	6	-	μC	$V_R=400V$, $I_F=11A$, $di_F/dt=55A/\mu s$
Peak reverse recovery current	I_{rrm}	-	16	-	A	$V_R=400V$, $I_F=11A$, $di_F/dt=55A/\mu s$

5 Electrical characteristics diagrams

Table 8

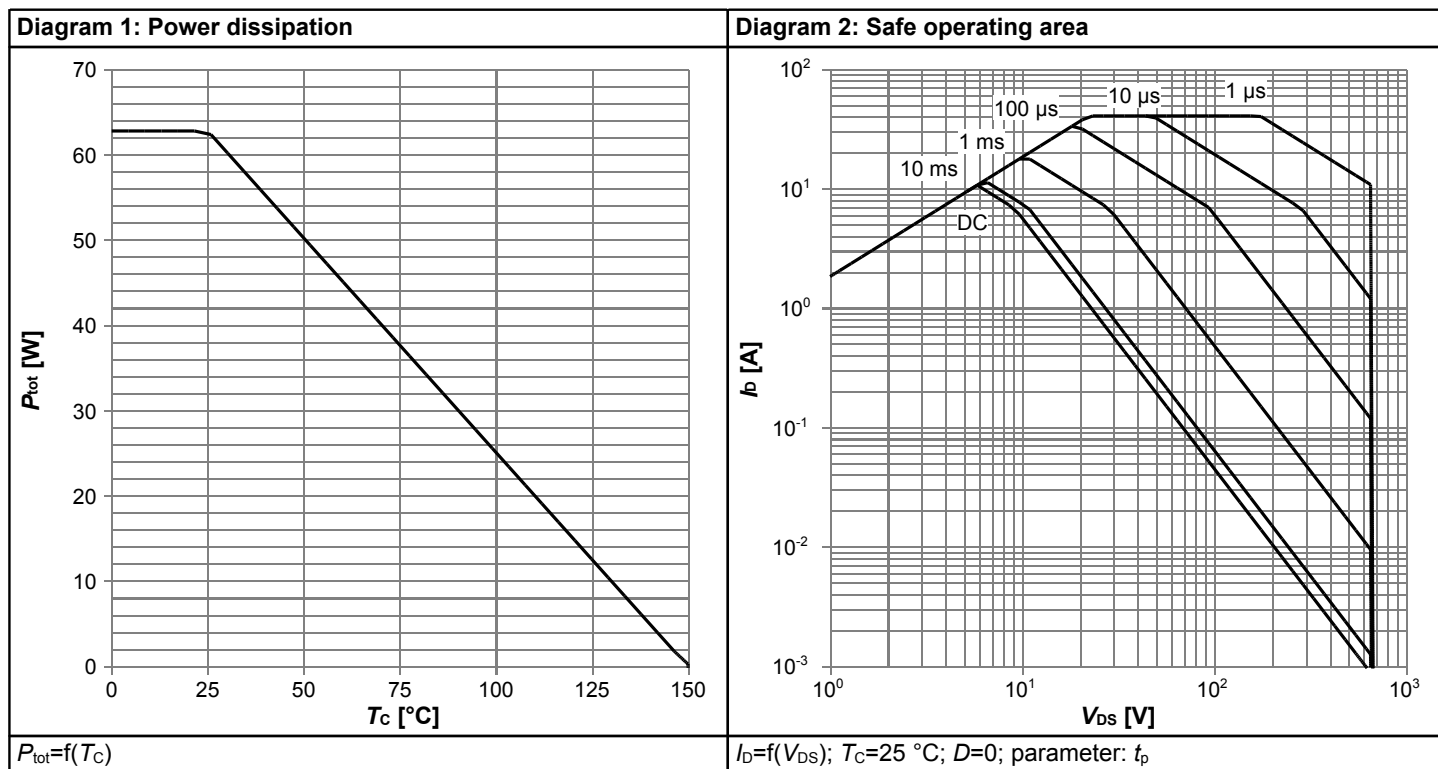


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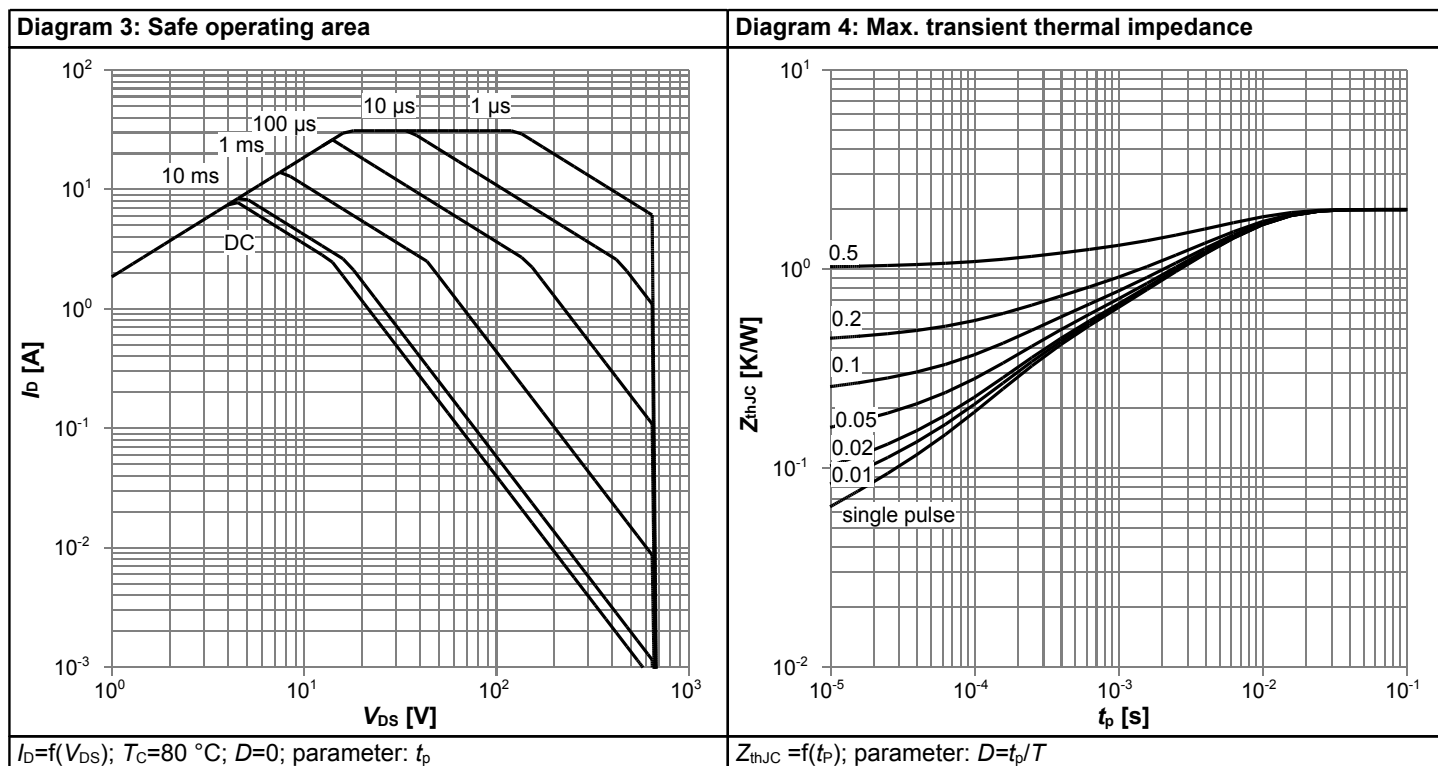


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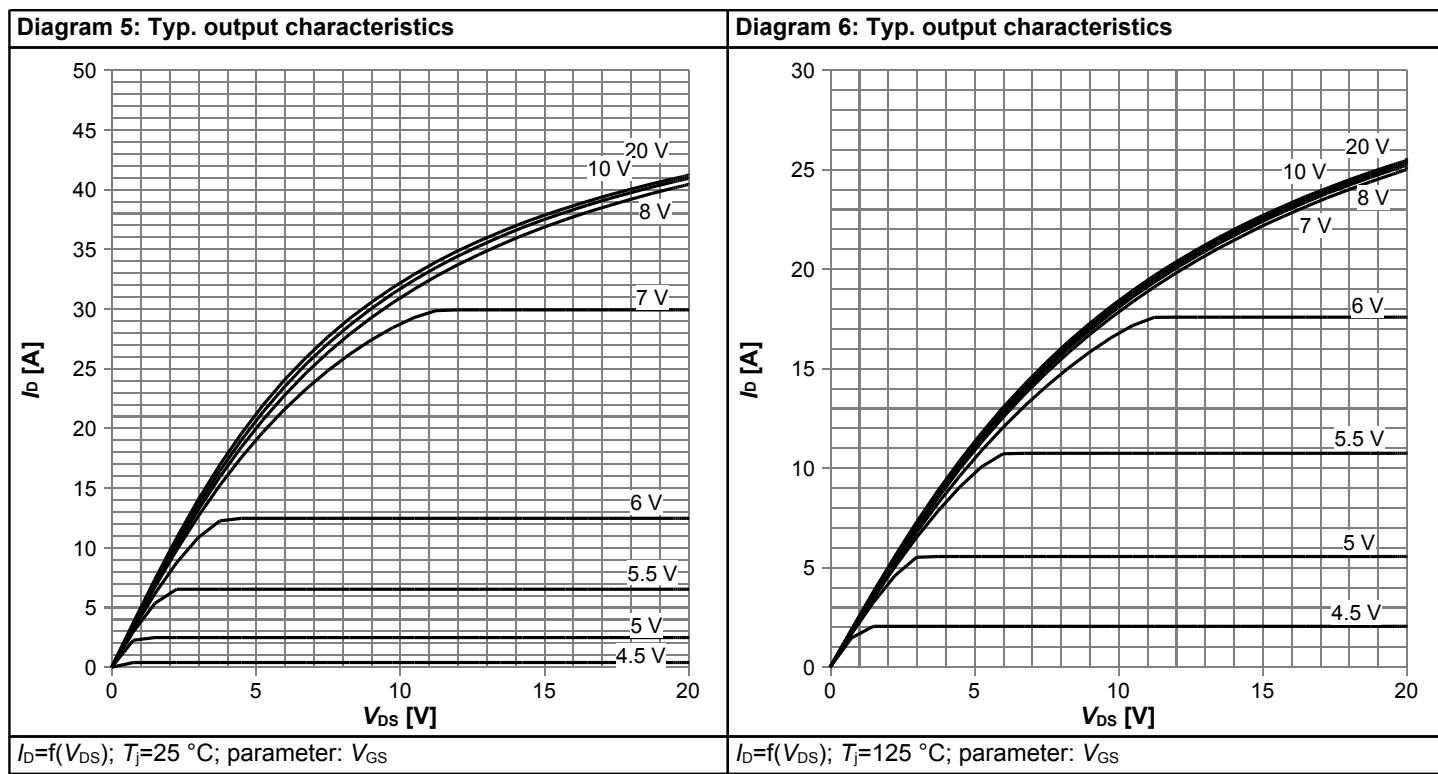


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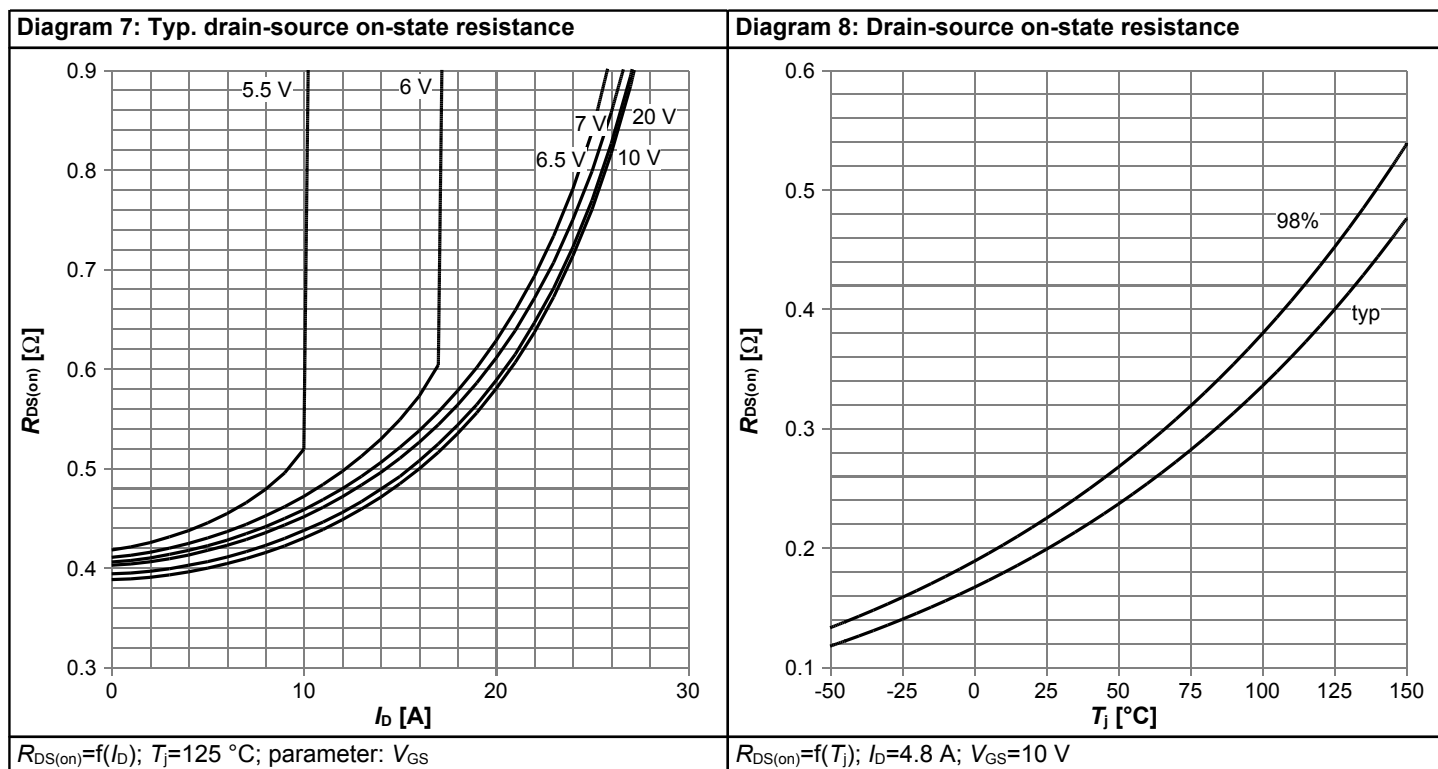


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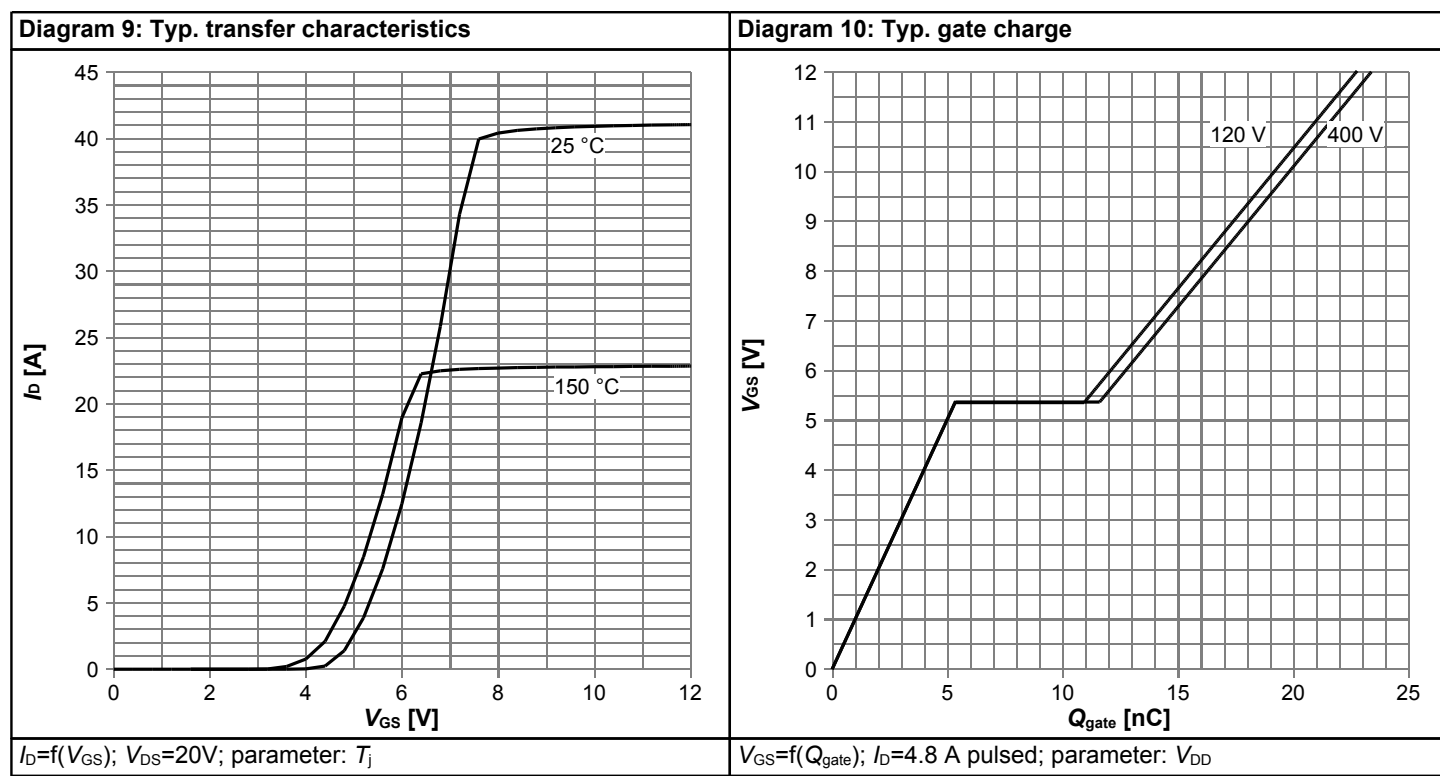


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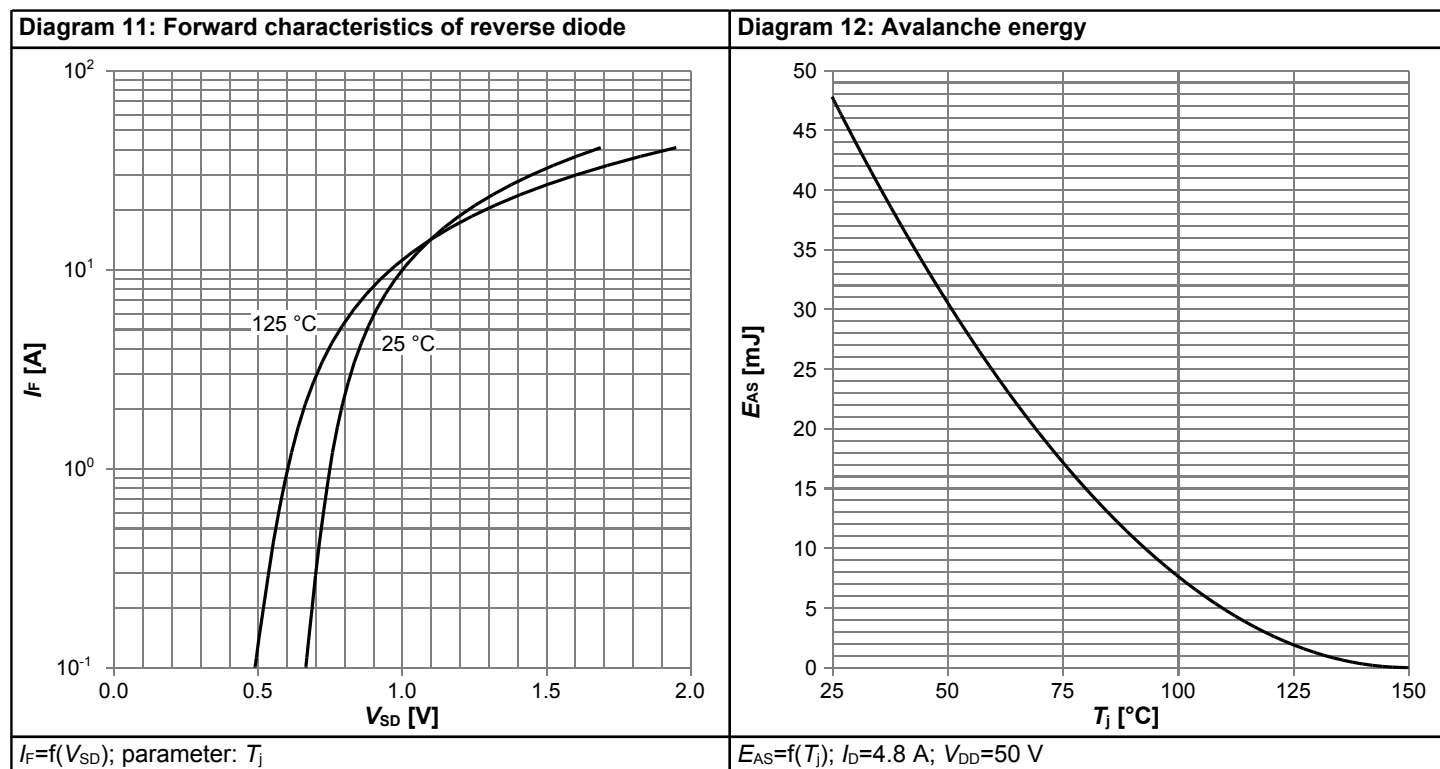


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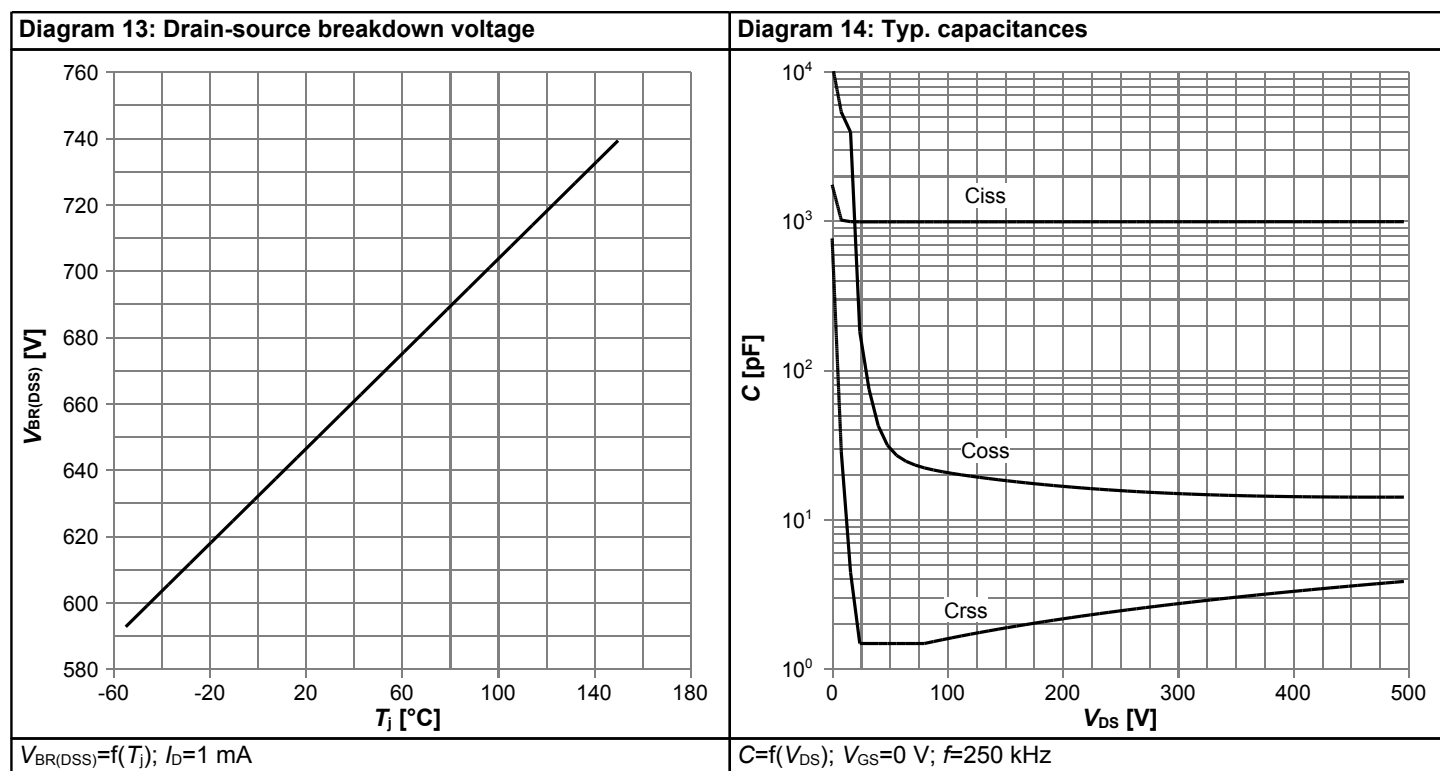
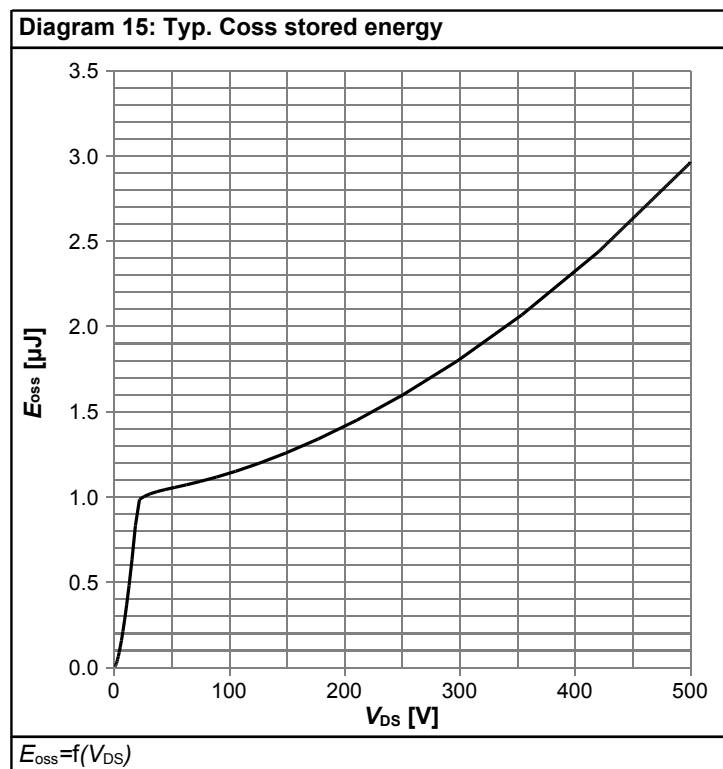


Table 15



6 Test Circuits

Table 16 Diode characteristics

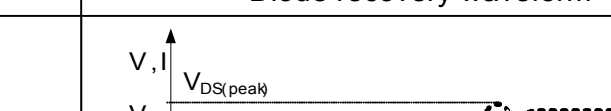
Test circuit for diode characteristics  $R_{g1} = R_{g2}$	Diode recovery waveform  $V_{DS(peak)}$ V_{DS} I_F t_F t_{tr} t_S dI_F/dt dI_{tr}/dt $10\% I_{rm}$ I_{rm} $t_{tr} = t_F + t_S$ $Q_{tr} = Q_F + Q_S$
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Table 17 Switching times

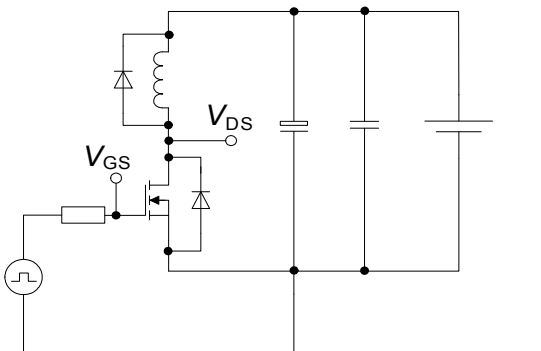
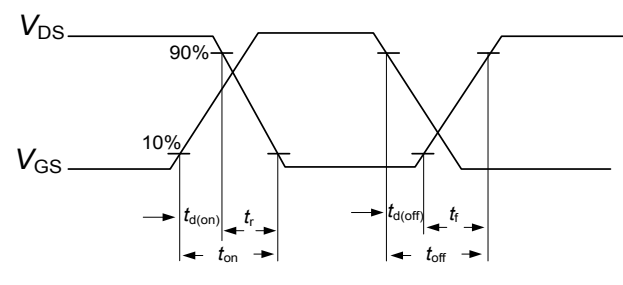
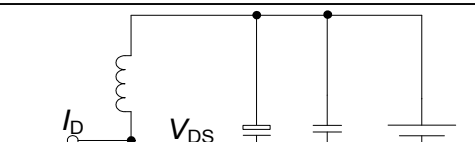
Switching times test circuit for inductive load	Switching times waveform
 The circuit diagram illustrates a MOSFET switching an inductive load. A DC voltage source is connected to the drain of the MOSFET through an inductor and a diode in parallel. The gate of the MOSFET is driven by a pulse generator connected through a gate resistor. The drain-source voltage V_{DS} is measured across the load, and the gate-source voltage V_{GS} is measured at the gate. The MOSFET's body diode is also shown.	 The waveform diagram shows the switching transitions for V_{DS} and V_{GS}. During the turn-on transition, V_{GS} rises from 10% to 90% of its peak, and V_{DS} falls from 90% to 10% of its peak. The time intervals labeled are $t_{d(on)}$ (delay time), t_r (rise time), and t_{on} (total turn-on time). During the turn-off transition, V_{GS} falls from 90% to 10% of its peak, and V_{DS} rises from 10% to 90% of its peak. The time intervals labeled are $t_{d(off)}$ (delay time), t_f (fall time), and t_{off} (total turn-off time).

Table 18 Unclamped inductive load

Unclamped inductive load test circuit	Unclamped inductive waveform
	

7 Package Outlines



Figure 1 Outline PG-TO 220, dimensions in mm/inches

8 Appendix A

Table 19 Related Links

- IFX CoolMOS™ C7 Webpage: www.infineon.com
- IFX CoolMOS™ C7 application note: www.infineon.com
- IFX CoolMOS™ C7 simulation model: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPP65R225C7

Revision: 2013-04-18, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2013-04-18	Release of final version

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